优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

Part Number	R1(NOM)	R2(NOM)	Marking
NK-DDTC144ELP	47kΩ	47kΩ	N6

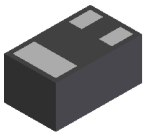
Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (NK-DDTA144ELP)
- Ultra-Small Leadless Surface Mount Package
- Ideally Suited for Automated Assembly Processes

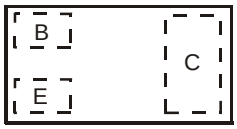
Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Marking Information
- Terminals: Finish — NiPdAu Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.001 grams (Approximate)

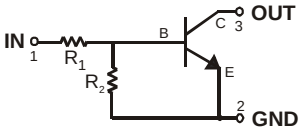
X1-DFN1006-3



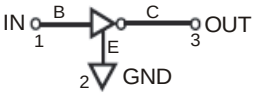
Bottom View



Top View
Pin-Out



Device Symbol



Equivalent Inverter Circuit

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage	V_{CC}	50	V
Input Voltage	V_{IN}	-10 to +40	V
Output Current	$I_{C(MAX)}$	100	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	250	mW
Power Deration above 25°C	P_{der}	2	mW/°C
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{\theta JA}$	500	°C/W
Operation and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	I_C = 50μA, I_E = 0
Collector-Emitter Breakdown Voltage (Note 6)	BV_{CEO}	50	—	—	V	I_C = 1.0mA, I_B = 0
Collector-Base Cut Off Current	I_{CBO}	—	—	0.5	μA	V_{CB} = 50V, I_E = 0
Input Voltage (Note 6)	$V_{I(OFF)}$	0.5	1.2	—	V	V_{CE} = 5V, I_O = 100μA
	$V_{I(ON)}$	—	1.6	3		V_{CE} = 0.3V, I_O = 2mA
Output Voltage (Note 6)	$V_{O(ON)}$	—	—	0.3	V	I_O/I_I = 10mA/0.5mA
Input Current	I_I	—	—	0.18	mA	V_I = 5V
Output Current	$I_{O(OFF)}$	—	—	0.5	μA	V_{CC} = 50V, V_I = 0V
DC Current Gain (Note 6)	G_1	68	—	—	—	V_O = 5V, I_O = 5mA
Input Resistance	R_1	32.9	47	61.1	kΩ	—
Resistance Ratio	R_2/R_1	0.8	1	1.2	—	—
Transition Frequency (Note 7)	f_T	—	250	—	MHz	V_{CE} = 10V, I_E = 5mA, f = 100MHz

Notes:
5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
6. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.
7. Characteristics of transistor only.

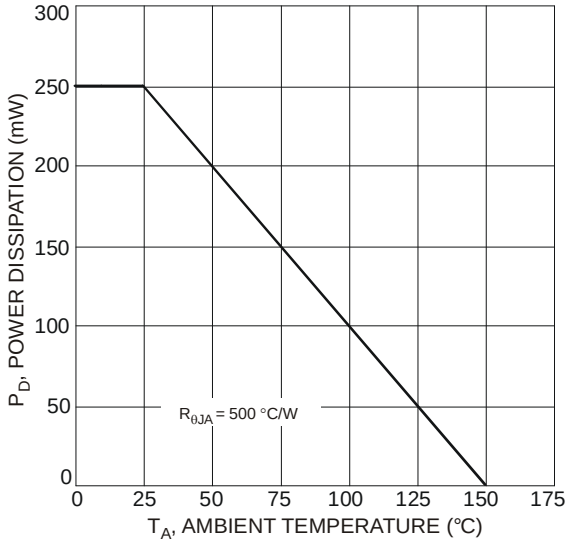


Fig. 1 Power Dissipation vs. Ambient Temperature

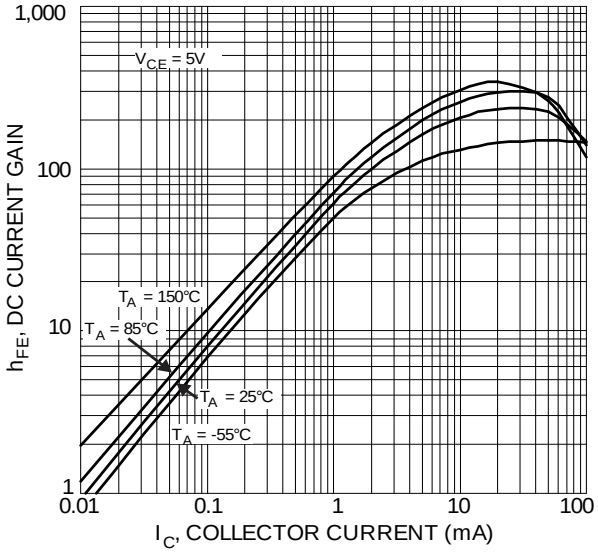


Fig. 2 Typical DC Current Gain vs. Collector Current

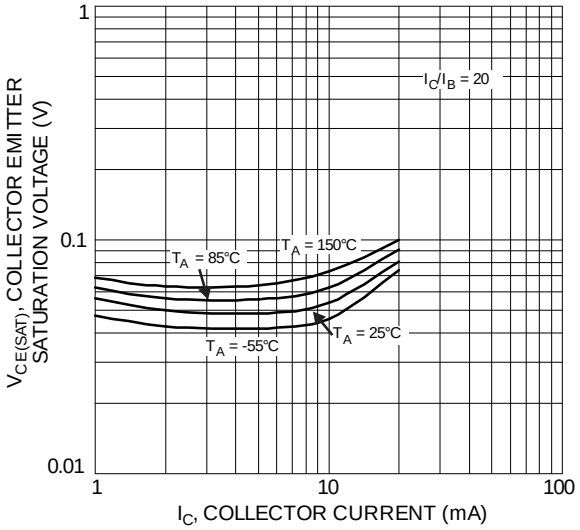


Fig. 3 Typical Collector Emitter Saturation Voltage vs. Collector Current

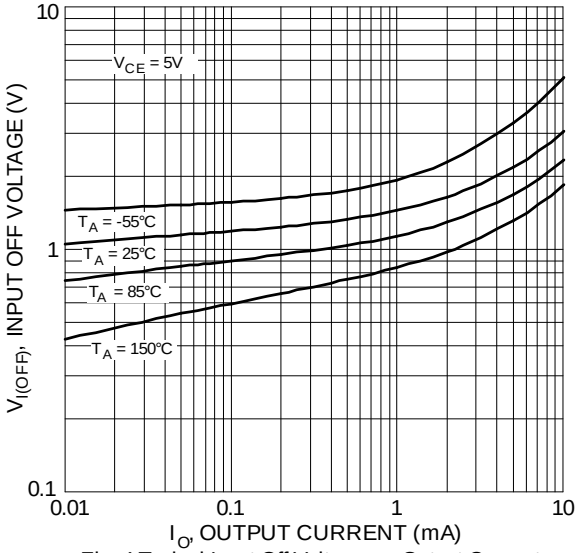


Fig. 4 Typical Input Off Voltage vs. Output Current

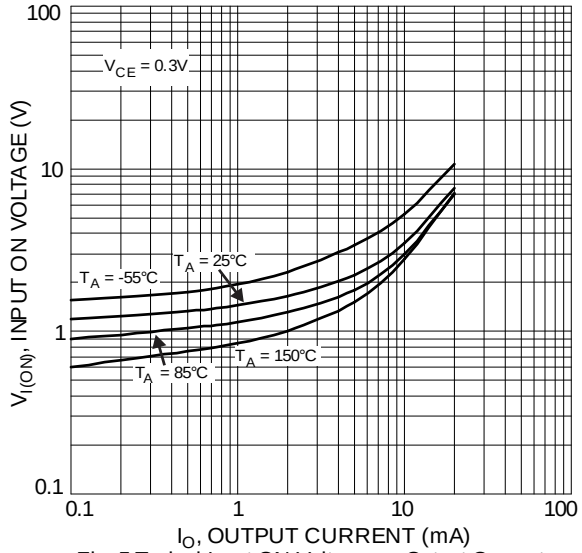
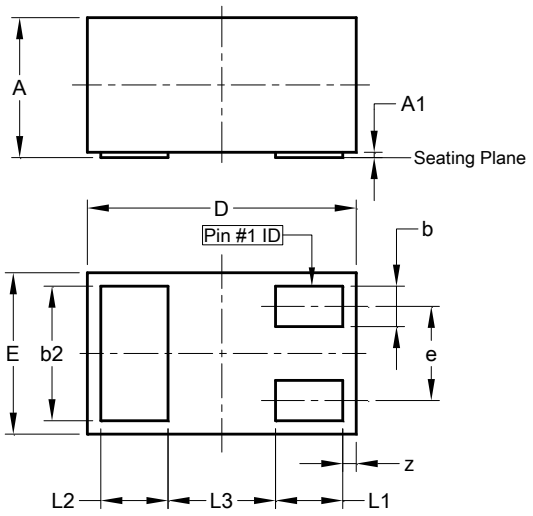


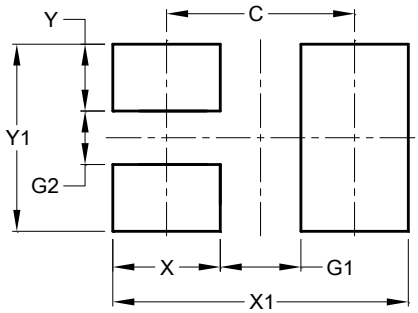
Fig. 5 Typical Input ON Voltage vs. Output Current

Package Outline Dimensions



X1-DFN1006-3			
Dim	**Min**	**Max**	**Typ**
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70